# MBD54DWT1G

Preferred Device

# **Dual Schottky Barrier Diodes**

These Schottky barrier diodes are designed for high speed switching applications, circuit protection, and voltage clamping. Extremely low forward voltage reduces conduction loss. Miniature surface mount package is excellent for hand held and portable applications where space is limited.

#### **Features**

- Extremely Fast Switching Speed
- Low Forward Voltage 0.35 V @ I<sub>F</sub> = 10 mAdc
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

# **MAXIMUM RATINGS** (T<sub>J</sub> = 125°C unless otherwise noted)

Rating	Symbol	Value	Unit
Reverse Voltage	V <sub>R</sub>	30	V
Forward Power Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>F</sub>	150 1.2	mW mW/°C
Forward Current (DC)	I <sub>F</sub>	200 Max	mA
Junction Temperature	TJ	125 Max	°C
Storage Temperature Range	T <sub>stg</sub>	-55 to +150	°C

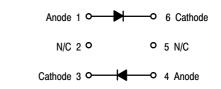
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

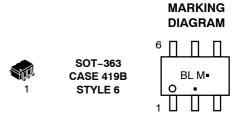


# ON Semiconductor®

http://onsemi.com

# 30 VOLTS DUAL HOT-CARRIER DETECTOR AND SWITCHING DIODES





M = Date Code ■ = Pb-Free Package

(Note: Microdot may be in either location)

#### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
MBD54DWT1G	SOT-363 (Pb-Free)	3000 / Tape & Reel

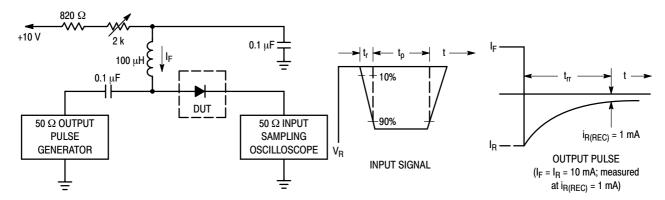
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

**Preferred** devices are recommended choices for future use and best overall value.

# MBD54DWT1G

# **ELECTRICAL CHARACTERISTICS** ( $T_A = 25$ °C unless otherwise noted) (EACH DIODE)

Characteristic	Symbol	Min	Тур	Max	Unit
Reverse Breakdown Voltage (I <sub>R</sub> = 10 μA)	V <sub>(BR)R</sub>	30	-	-	V
Total Capacitance (V <sub>R</sub> = 1.0 V, f = 1.0 MHz)	C <sub>T</sub>	-	7.6	10	pF
Reverse Leakage (V <sub>R</sub> = 25 V)	I <sub>R</sub>	-	0.5	2.0	μAdc
Forward Voltage (I <sub>F</sub> = 0.1 mAdc)	V <sub>F</sub>	-	0.22	0.24	Vdc
Forward Voltage (I <sub>F</sub> = 30 mAdc)	V <sub>F</sub>	-	0.41	0.5	Vdc
Forward Voltage (I <sub>F</sub> = 100 mAdc)	V <sub>F</sub>	-	0.52	1.0	Vdc
Reverse Recovery Time ( $I_F = I_R = 10 \text{ mAdc}$ , $I_{R(REC)} = 1.0 \text{ mAdc}$ ) (Figure 1)	t <sub>rr</sub>	-	_	5.0	ns
Forward Voltage (I <sub>F</sub> = 1.0 mAdc)	V <sub>F</sub>	-	0.29	0.32	Vdc
Forward Voltage (I <sub>F</sub> = 10 mAdc)	V <sub>F</sub>	-	0.35	0.40	Vdc
Forward Current (DC)	I <sub>F</sub>	-	-	200	mAdc
Repetitive Peak Forward Current	I <sub>FRM</sub>	-	-	300	mAdc
Non-Repetitive Peak Forward Current (t < 1.0 s)	I <sub>FSM</sub>	-	-	600	mAdc

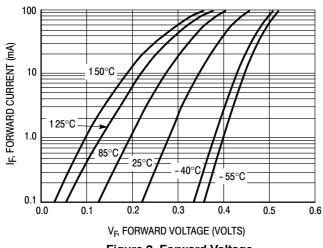


Notes: 1. A 2.0 k $\Omega$  variable resistor adjusted for a Forward Current (IF) of 10 mA.

- 2. Input pulse is adjusted so  $I_{R(peak)}$  is equal to 10 mA.
- 3.  $t_p * t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

# MBD54DWT1G



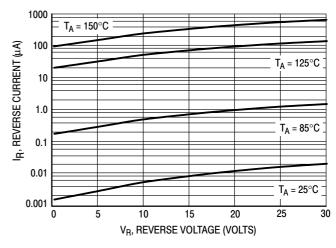


Figure 2. Forward Voltage

Figure 3. Leakage Current

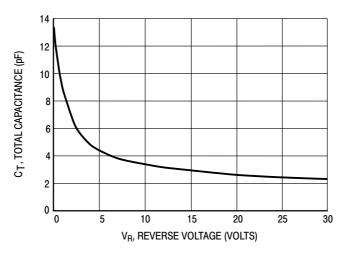


Figure 4. Total Capacitance

# SC-88/SC70-6/SOT-363 CASE 419B-02 **ISSUE Y**

**DATE 11 DEC 2012** 





# NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
   CONTROLLING DIMENSION: MILLIMETERS
- CONTROLLING DIMENSION: MILLIMETERS.
  DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH,
- DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H. DATUMS A AND B ARE DETERMINED AT DATUM H. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.

- DIMENSION & DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION 6 AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α			1.10			0.043
A1	0.00		0.10	0.000		0.004
A2	0.70	0.90	1.00	0.027	0.035	0.039
b	0.15	0.20	0.25	0.006	0.008	0.010
С	0.08	0.15	0.22	0.003	0.006	0.009
D	1.80	2.00	2.20	0.070	0.078	0.086
E	2.00	2.10	2.20	0.078	0.082	0.086
E1	1.15	1.25	1.35	0.045	0.049	0.053
е		0.65 BS	С	0.026 BSC		
L	0.26	0.36	0.46	0.010	0.014	0.018
L2	0.15 BSC 0.006 BSC			SC		
aaa	0.15				0.006	
bbb	0.30			0.012		
ccc	0.10			0.004		
ddd	0.10				0.004	

# **GENERIC MARKING DIAGRAM\***



XXX = Specific Device Code

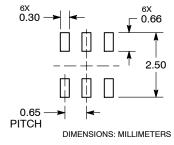
= Date Code\*

= Pb-Free Package

(Note: Microdot may be in either location)

- \*Date Code orientation and/or position may vary depending upon manufacturing location.
- \*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

#### **RECOMMENDED SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# **STYLES ON PAGE 2**

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**DATE 11 DEC 2012** 

STYLE 1: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2	STYLE 2: CANCELLED	STYLE 3: CANCELLED	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. COLLECTOR 4. EMITTER 5. BASE 6. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	STYLE 6: PIN 1. ANODE 2 2. N/C 3. CATHODE 1 4. ANODE 1 5. N/C 6. CATHODE 2
STYLE 7: PIN 1. SOURCE 2 2. DRAIN 2 3. GATE 1 4. SOURCE 1 5. DRAIN 1 6. GATE 2	STYLE 8: CANCELLED	STYLE 9: PIN 1. EMITTER 2 2. EMITTER 1 3. COLLECTOR 1 4. BASE 1 5. BASE 2 6. COLLECTOR 2	STYLE 10: PIN 1. SOURCE 2 2. SOURCE 1 3. GATE 1 4. DRAIN 1 5. DRAIN 2 6. GATE 2	STYLE 11: PIN 1. CATHODE 2 2. CATHODE 2 3. ANODE 1 4. CATHODE 1 5. CATHODE 1 6. ANODE 2	STYLE 12: PIN 1. ANODE 2 2. ANODE 2 3. CATHODE 1 4. ANODE 1 5. ANODE 1 6. CATHODE 2
STYLE 13: PIN 1. ANODE 2. N/C 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	STYLE 14: PIN 1. VREF 2. GND 3. GND 4. IOUT 5. VEN 6. VCC	STYLE 15: PIN 1. ANODE 1 2. ANODE 2 3. ANODE 3 4. CATHODE 3 5. CATHODE 2 6. CATHODE 1	STYLE 16: PIN 1. BASE 1 2. EMITTER 2 3. COLLECTOR 2 4. BASE 2 5. EMITTER 1 6. COLLECTOR 1	STYLE 17: PIN 1. BASE 1 2. EMITTER 1 3. COLLECTOR 2 4. BASE 2 5. EMITTER 2 6. COLLECTOR 1	STYLE 18: PIN 1. VIN1 2. VCC 3. VOUT2 4. VIN2 5. GND 6. VOUT1
STYLE 19: PIN 1. I OUT 2. GND 3. GND 4. V CC 5. V EN 6. V REF	STYLE 20: PIN 1. COLLECTOR 2. COLLECTOR 3. BASE 4. EMITTER 5. COLLECTOR 6. COLLECTOR	STYLE 21: PIN 1. ANODE 1 2. N/C 3. ANODE 2 4. CATHODE 2 5. N/C 6. CATHODE 1	STYLE 22: PIN 1. D1 (i) 2. GND 3. D2 (i) 4. D2 (c) 5. VBUS 6. D1 (c)	STYLE 23: PIN 1. Vn 2. CH1 3. Vp 4. N/C 5. CH2 6. N/C	STYLE 24: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE
STYLE 25: PIN 1. BASE 1 2. CATHODE 3. COLLECTOR 2 4. BASE 2 5. EMITTER 6. COLLECTOR 1	STYLE 26: PIN 1. SOURCE 1 2. GATE 1 3. DRAIN 2 4. SOURCE 2 5. GATE 2 6. DRAIN 1	STYLE 27: PIN 1. BASE 2 2. BASE 1 3. COLLECTOR 1 4. EMITTER 1 5. EMITTER 2 6. COLLECTOR 2	STYLE 28: PIN 1. DRAIN 2. DRAIN 3. GATE 4. SOURCE 5. DRAIN 6. DRAIN	STYLE 29: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE/ANODE 6. CATHODE	STYLE 30: PIN 1. SOURCE 1 2. DRAIN 2 3. DRAIN 2 4. SOURCE 2 5. GATE 1 6. DRAIN 1

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

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